List of research papers written by our customers using our GaN epitaxial wafers

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NTT Advanced Technology Corporation (NTT-AT) has been providing gallium nitride (GaN) epitaxial wafers for academic and industrial R&D fields. Nitride semiconductors have capability of high output, high withstand voltage, high frequency, and low loss operation, and its power electric devices are expected to support the low-carbon society. In this document, we present customers' publications from 2020 to 2024 for your references. You can also find our product detail from the link below;
https://keytech.ntt-at.co.jp/en/epi/prd_1002.html

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